<u>TOSHIBA</u>

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

HN1B04FU

Audio Frequency General Purpose Amplifier Applications

Unit: mm

 $Q1:\!\mathrm{High}$ voltage and high current

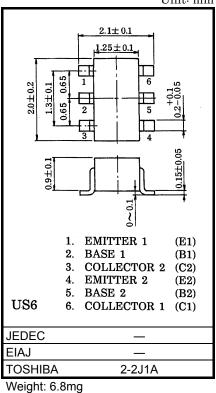
- $: V_{CEO} = 50V, I_C = 150mA (max)$
- High h_{FE} : $h_{FE} = 120 \sim 400$
- Excellent hFE linearity

 $h_{\rm FE}$ (IC = 0.1mA) / h_{FE} (IC = 2mA) = 0.95 (typ.)

Q2:

- High voltage and high current
 - $: V_{CEO} = -50V, I_{C} = -150mA (max)$
- High h_{FE} : $h_{FE} = 120 \sim 400$
- Excellent hFE linearity

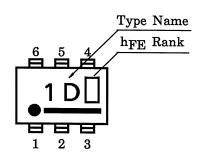
: $h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 (typ.)$



Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ι _C	150	mA
Base current	Ι _Β	30	mA

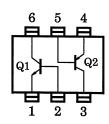
Marking



Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-150	mA
Base current	Ι _Β	-30	mA

Equivalent Circuit (Top View)



Q1,Q2 Common Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

* Total rating

Q1 Electrical Characteristics (Ta = 25°C)

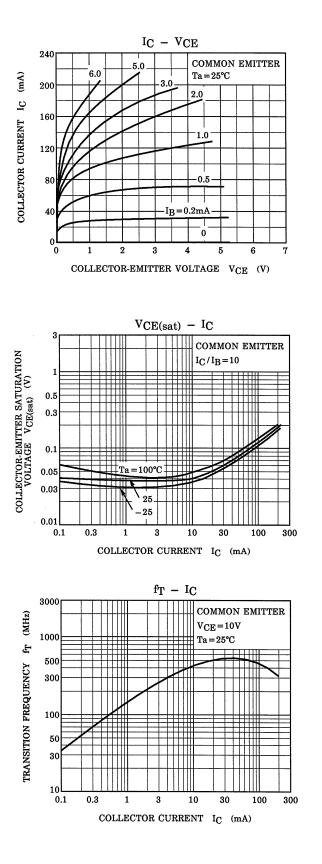
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = 60V, I_E = 0$	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	-	V _{EB} = 5V, I _C = 0		-	0.1	μA
DC current gain	h _{FE (Note)}	_	V _{CE} = 6V, I _C = 2mA	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	_	0.1	0.25	V
Transition frequency	fT	_	V _{CE} = 10V, I _C = 1mA	_	150	_	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = 10V, I _E = 0, f = 1MHz	_	2	_	pF

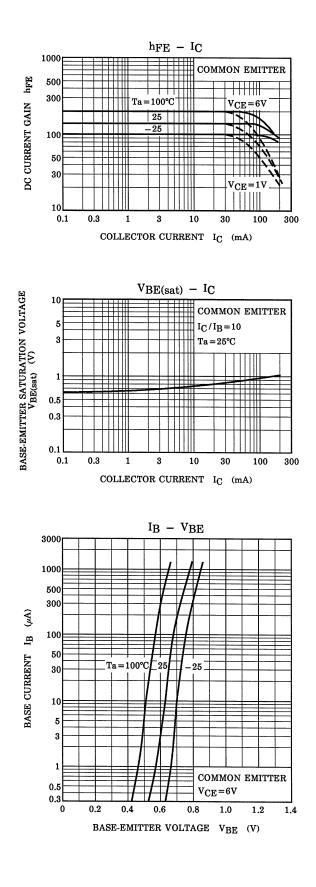
Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V, I_E = 0$	_	_	-0.1	μA
Emitter cut-off current	I _{EBO}	—	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h _{FE (Note)}	_	$V_{CE} = -6V, I_C = -2mA$	120		400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -100mA, I _B = -10mA		-0.1	-0.3	V
Transition frequency	f _T	_	V _{CE} = -10V, I _C = -1mA	_	120	_	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = -10V, I _E = 0, f = 1MHz	_	4	_	pF

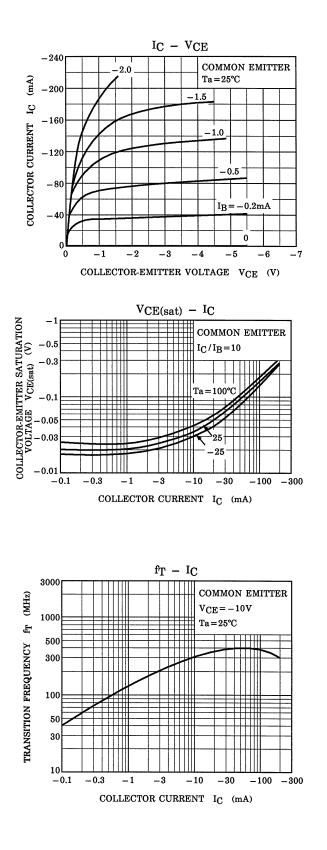
Note: hFE Classification Y (Y): 120~240, GR (G): 200~400 () Marking Symbol

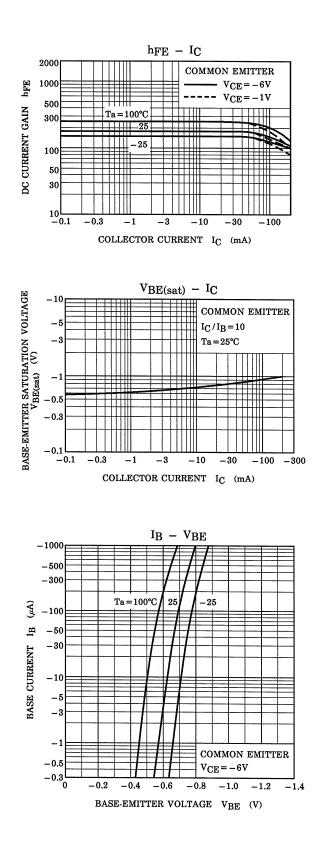
Q1 (NPN transistor)





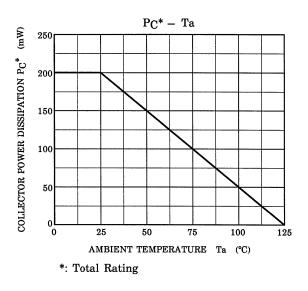
Q2 (PNP transistor)





TOSHIBA

(Q1, Q2 Common)



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20070701-EN GENERAL

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